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n-Type Conducting P doped ZnO Thin Films via Chemical Vapor Deposition

Donglei Zhao, Jianwei Li, Sanjayan Sathasivam and Claire J. Carmalt*

*Corresponding author

Materials Chemistry Centre, Department of Chemistry, University College London, 20 Gordon Street, London WC1H 0AJ, UK

Fax: (+44) 20-7679-7463

E-mail: <u>c.j.carmalt@ucl.ac.uk</u>

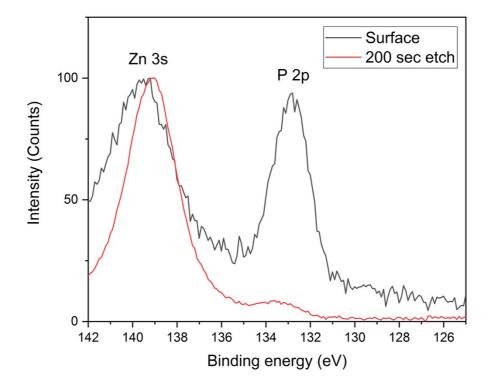


Figure S1: Depth profiling of the 14.3 at.% P doped ZnO films showing P to be highly surface segregated. XPS results show 52% P relative to Zn on the surface and only 2% after 200 seconds of etching